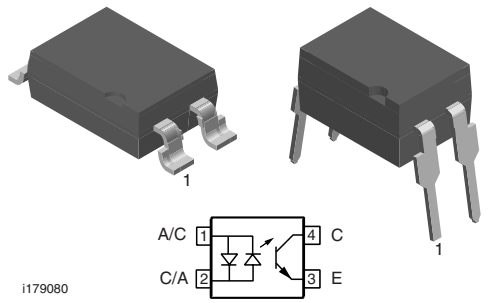
Optocoupler, Phototransistor Output, AC Input



FEATURES

- Good CTR linearity depending on forward current
- Isolation test voltage, 5300 V_{RMS}
- High collector emitter voltage, V_{CEO} = 70 V
- Low saturation voltage
- Fast switching times
- Low CTR degradation
- Temperature stable
- Low coupling capacitance
- End-stackable, 0.100" (2.54 mm) spacing
- High common-mode interference immunity
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Pb-free

e3

RoHS COMPLIANT

DESCRIPTION

The SFH620A (DIP) and SFH6206 (SMD) feature a high current transfer ratio, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 or SMD package.

The coupling devices are designed for signal transmission between two electrically separated circuits. The couplers are end-stackable with 2.54 mm lead spacing. Creepage and clearance distances of > 8.0 mm are achieved with option 6. This version complies with IEC 60950 (DIN VDE 0805) for reinforced insulation to an operation voltage of 400 V_{RMS} or DC.

AGENCY APPROVALS

- UL1577, file no. E52744 system code J
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-5 (VDE 0884) available with option 1

ORDER INFORMATION	
PART	**REMARKS**
SFH620A-1	CTR 40 to 125 %, DIP-4
SFH620A-2	CTR 63 to 200 %, DIP-4
SFH620A-3	CTR 100 to 320 %, DIP-4
SFH6206-1	CTR 40 to 125 %, SMD-4
SFH6206-2	CTR 63 to 200 %, SMD-4
SFH6206-3	CTR 100 to 320 %, SMD-4
SFH620A-1-X006	CTR 40 to 125 %, DIP-4 mil (option 6)
SFH620A-2-X006	CTR 63 to 200 %, DIP-4mil (option 6)
SFH620A-2-X007	CTR 63 to 200 %, SMD-4 (option 7)
SFH620A-3-X006	CTR 100 to 320 %, DIP-4 mil (option 6)

Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS (1)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
DC forward current		I_F	± 60	mA
Surge forward current	$t_p \leq 10$ µs	I_{FSM}	± 2.5	A
Power dissipation		P_{diss}	100	mW
OUTPUT				
Collector emitter voltage		V_{CE}	70	V
Emitter collector voltage		V_{EC}	7	V
Collector current		I_C	50	mA
	$t_p \leq 1.0$ µs	I_C	100	mA
Power dissipation		P_{diss}	150	mW
COUPLER				
Isolation test voltage between emitter and detector		V_{ISO}	5300	V_{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Insulation thickness between emitter and detector			≥ 4	mm
Comparative tracking index per DIN IEC112/ VDE 0303, part 1		CTI	175	
Isolation resistance	V_{IO} = 500 V, T_{amb} = 25 °C	R_{IO}	$\geq 10^{12}$	Ω
	V_{IO} = 500 V, T_{amb} = 100 °C	R_{IO}	$\geq 10^{11}$	Ω
Storage temperature range		T_{stg}	- 55 to + 150	°C
Ambient temperature range		T_{amb}	- 55 to + 100	°C
Junction temperature		T_j	100	°C
Soldering temperature (2)	max. 10 s, dip soldering distance to seating plane ≥ 1.5 mm	T_{sld}	260	°C

Notes

(1) T_{amb} = 25 °C, unless otherwise specified.
Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	I_F = ± 60 mA		V_F		1.25	1.65	V
Capacitance	V_R = 0 V, f = 1 MHz		C_O		50		pF
Thermal resistance			R_{thja}		750		K/W
OUTPUT							
Collector emitter capacitance	V_{CE} = 5 V, f = 1 MHz		C_{CE}		6.8		pF
Thermal resistance			R_{thja}		500		°C/W
COUPLER							
Collector emitter saturation voltage	I_F = 10 mA, I_C = 2.5 mA		V_{CEsat}		0.25	0.4	V
Coupling capacitance			C_C		0.2		pF
Collector emitter leakage current	V_{CE} = 10 V	SFH620A-1	I_{CEO}		2	50	nA
		SFH6206-1	I_{CEO}		2	50	nA
		SFH620A-2	I_{CEO}		2	50	nA
		SFH6206-2	I_{CEO}		2	50	nA
		SFH620A-3	I_{CEO}		5	100	nA
		SFH6206-3	I_{CEO}		5	100	nA

Note

T_{amb} = 25 °C, unless otherwise specified.
Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.
Still air, coupler soldered to PCB or base.

CURRENT TRANSFER RATIO							
PARAMETER	**TEST CONDITION**	**PART**	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
I_C/I_F	V_{CE} = 5 V, I_F = ± 10 mA	SFH620A-1	CTR	40		125	%
		SFH6206-1	CTR	40		125	%
		SFH620A-2	CTR	63		200	%
		SFH6206-2	CTR	63		200	%
		SFH620A-3	CTR	100		320	%
		SFH6206-3	CTR	100		320	%
	V_{CE} = 5 V, I_F = ± 1 mA	SFH620A-1	CTR	13	30		%
		SFH6206-1	CTR	13	30		%
		SFH620A-2	CTR	22	45		%
		SFH6206-2	CTR	22	45		%
		SFH620A-3	CTR	34	70		%
		SFH6206-3	CTR	34	70		%

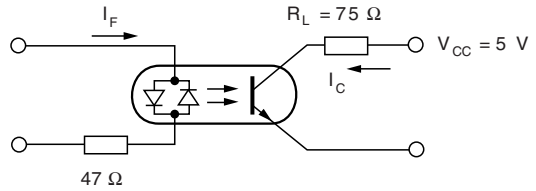


Fig. 1 - Switching Times Linear Operation (without Saturation)

SWITCHING CHARACTERISTICS						
PARAMETER	**TEST CONDITION**	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Turn-on time	R_L = 75 Ω, I_F = 10 mA, V_{CC} = 5 V	t_{on}		3		µs
Rise time	R_L = 75 Ω, I_F = 10 mA, V_{CC} = 5 V	t_r		2		µs
Turn-off time	R_L = 75 Ω, I_F = 10 mA, V_{CC} = 5 V	t_{off}		2.3		µs
Fall time	R_L = 75 Ω, I_F = 10 mA, V_{CC} = 5 V	t_f		2		µs
Cut-off frequency	R_L = 75 Ω, I_F = 10 mA, V_{CC} = 5 V	t_{ctr}		250		kHz

SAFETY AND INSULATION RATINGS						
PARAMETER	**TEST CONDITION**	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
V_{IOTM}			10000			V
V_{IORM}			890			V
P_{SO}					400	mW
I_{SI}					275	mA
T_{SI}					175	°C
Creepage distance	standard DIP-4		7			mm
Clearance distance	standard DIP-4		7			mm
Creepage distance	400 mil DIP-4		8			mm
Clearance distance	400 mil DIP-4		8			mm
Insulation thickness, reinforced rated	per IEC 60950 2.10.5.1		0.4			mm

Note

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

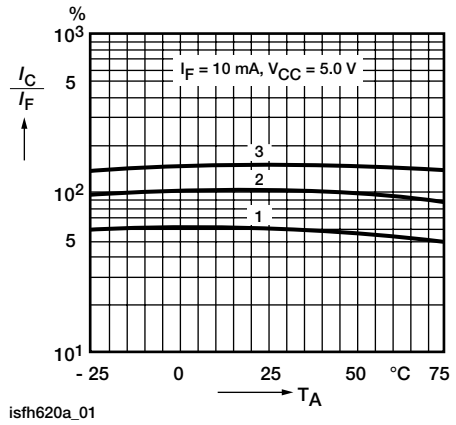


Fig. 2 - Current Transfer Ratio (CTR) vs. Temperature

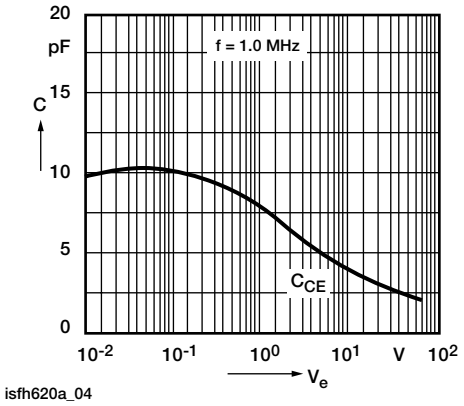


Fig. 5 - Transistor Capacitance (Typ.) vs. Collector Emitter Voltage

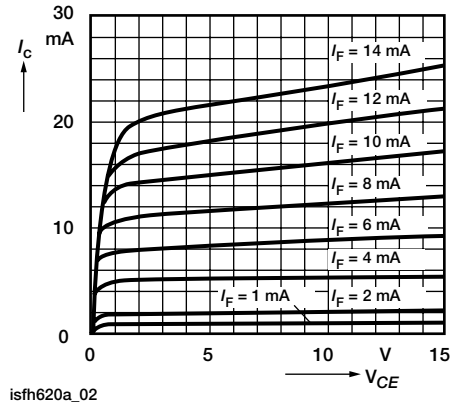


Fig. 3 - Output Characteristics (Typ.) Collector Current vs. Collector Emitter Voltage

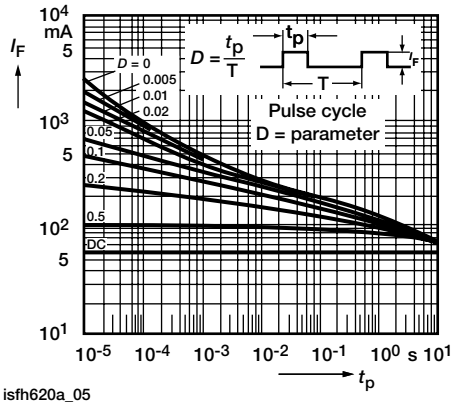


Fig. 6 - Permissible Pulse Handling Capability Forward Current vs. Pulse Width

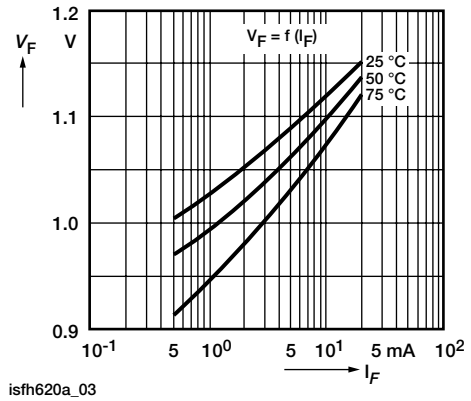


Fig. 4 - Diode Forward Voltage (Typ.) vs. Forward Current

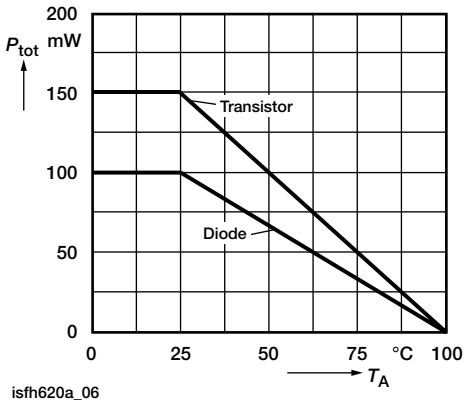


Fig. 7 - Permissible Power Dissipation vs. Ambient Temperature

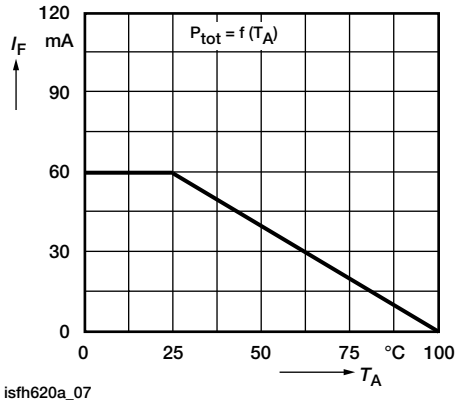
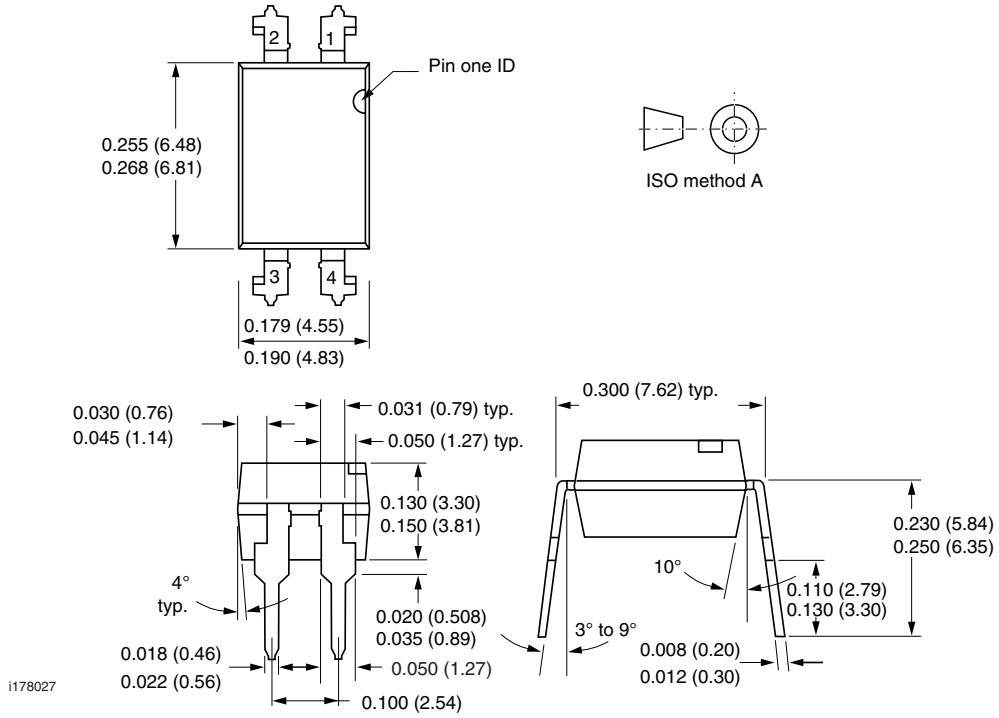
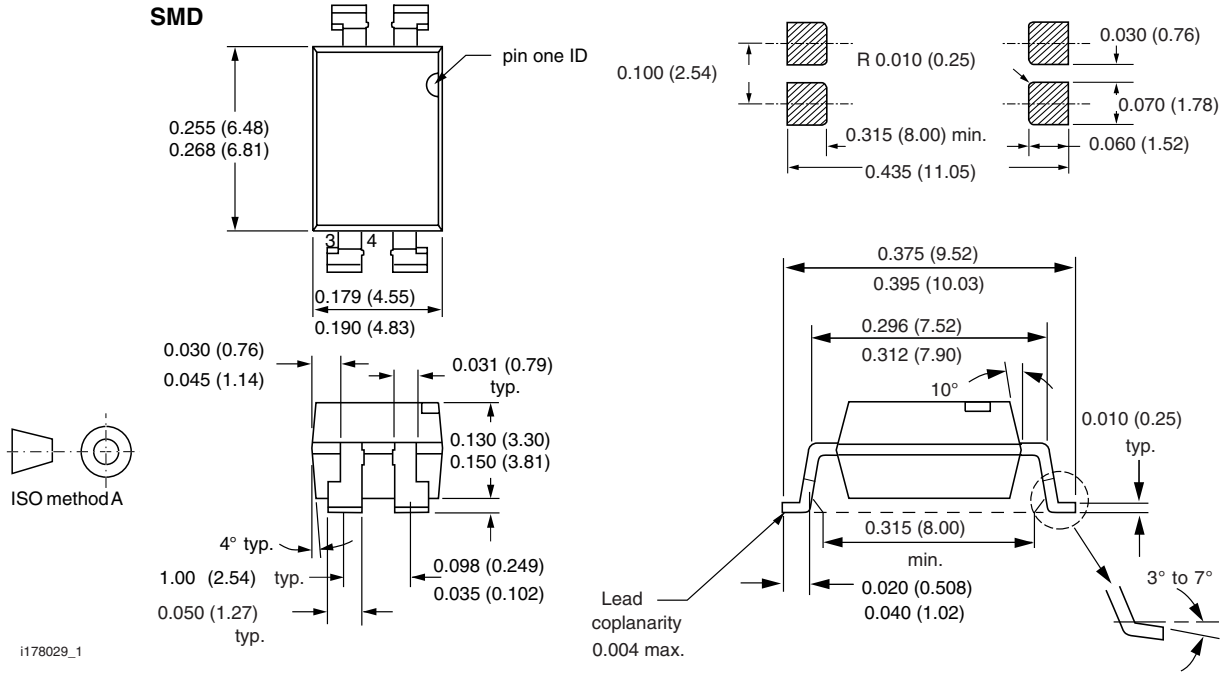


Fig. 8 - Permissible Diode Forward Current vs. Ambient Temperature

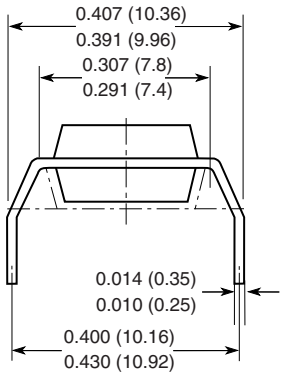
PACKAGE DIMENSIONS in inches (millimeters)



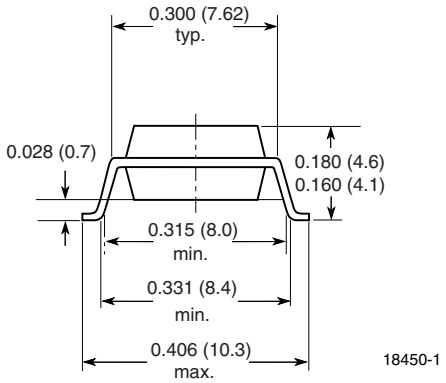
PACKAGE DIMENSIONS in inches (millimeters)



Option 6



Option 7



OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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